



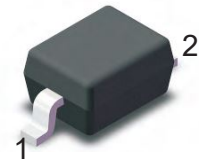
1N5817WS~1N5819WS

Schottky Barrier Diodes

Features

- High surge capability
- Low forward voltage drop
- Guarding for overvoltage protection
- Metal silicon junction, majority carrier conduction

SOD-323



1.Cathode —  — 2.Anode

Marking Code :

1N5817WS: SJ

1N5818WS: SK

1N5819WS: SL

Maximum Ratings and Electrical Characteristics

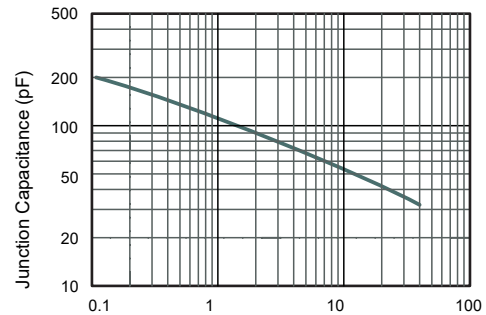
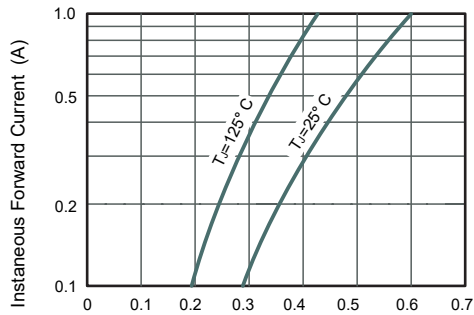
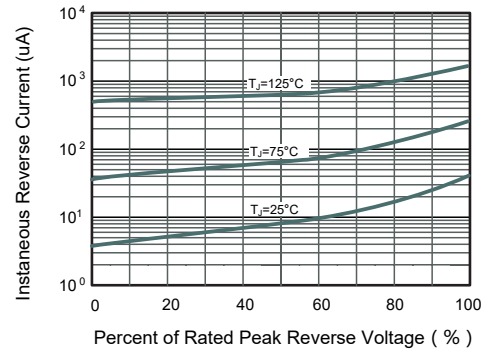
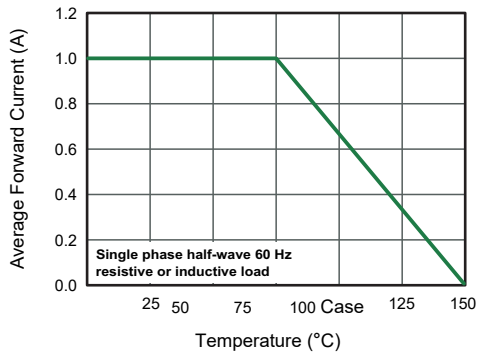
Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbols	1N5817WS	1N5818WS	1N5819WS	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	V
Maximum RMS Voltage	V_{RMS}	14	21	28	V
Maximum DC Blocking Voltage	V_{DC}	20	30	40	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1.0			A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	9			A
Maximum Instantaneous Forward Voltage	V_F	0.45	0.55	0.6	V
at 1 A		0.75	0.875	0.9	
Maximum DC Reverse Current at Rated DC Blocking Voltage	I_R				mA
at $T_A = 25^\circ\text{C}$		1			
at $T_A = 100^\circ\text{C}$	10				
Typical Junction Capacitance	C_j	110			pF
Operating Junction Temperature	T_J	150			°C
Storage Temperature Range	T_{STG}	-55 to +150			°C



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Typical Characteristic Curves





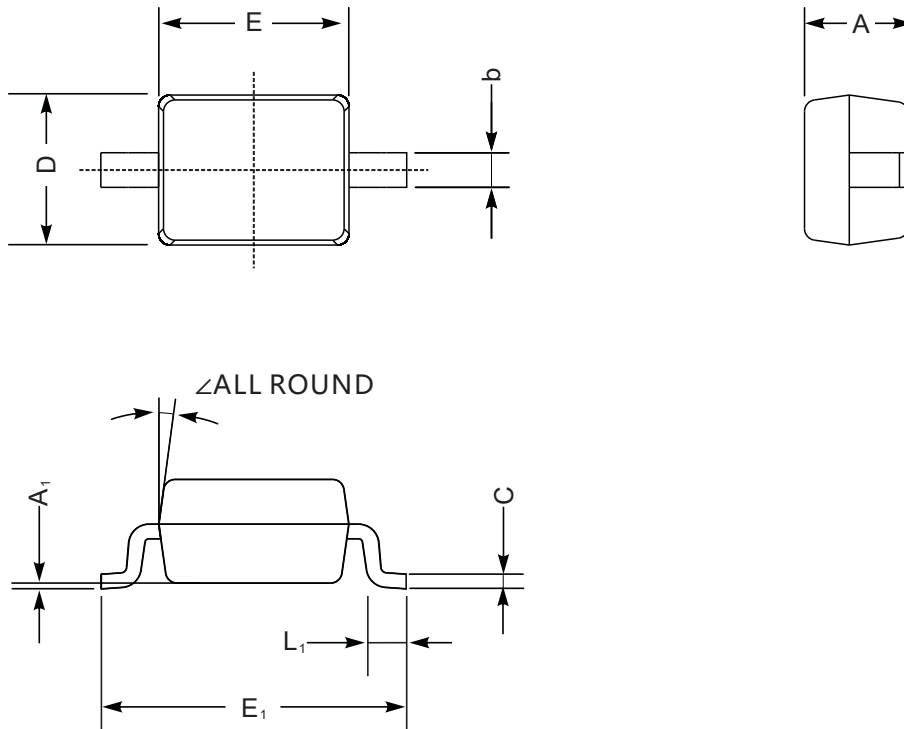
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Package Outline

SOD-323

Dimensions in mm



UNIT		A	C	D	E	E ₁	b	L ₁	A ₁	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	